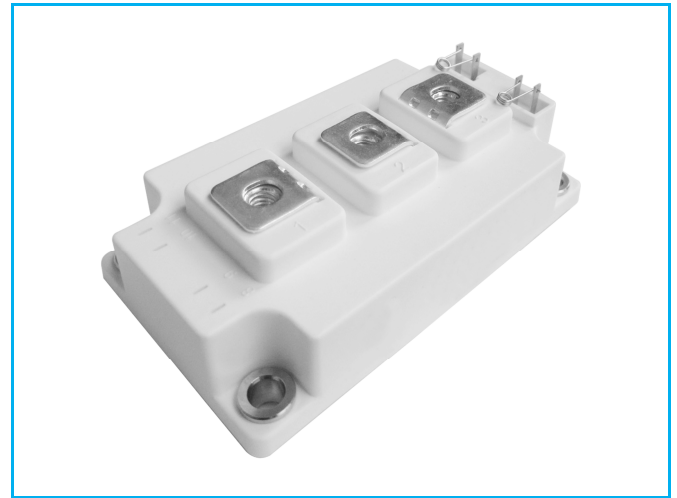


## PRODUCT FEATURES

- IGBT CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$  with positive temperature coefficient
- Ultra Low Loss,High Ruggedness
- Free wheeling diodes with fast and soft reverse recovery



## APPLICATIONS

- AC motor control
- Motion/servo control
- Inverter and power supplies
- Photovoltaic/Fuel cell

### IGBT-inverter

ABSOLUTE MAXIMUM RATINGS( $T_C=25^{\circ}C$  unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
$V_{CES}$	Collector Emitter Voltage	$T_J=25^{\circ}C$	1700	V
$V_{GES}$	Gate Emitter Voltage		$\pm 20$	
$I_C$	DC Collector Current	$T_C=25^{\circ}C, T_{Jmax}=175^{\circ}C$	155	A
		$T_C=100^{\circ}C, T_{Jmax}=175^{\circ}C$	100	
$I_{CM}$	Repetitive Peak Collector Current	$t_p=1ms$	200	
$P_{tot}$	Power Dissipation Per IGBT	$T_C=25^{\circ}C, T_{Jmax}=175^{\circ}C$	789	W

### Diode-inverter

ABSOLUTE MAXIMUM RATINGS ( $T_C=25^{\circ}C$  unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
$V_{RRM}$	Repetitive Reverse Voltage	$T_J=25^{\circ}C$	1700	V
$I_{F(AV)}$	Average Forward Current		100	A
$I_{FRM}$	Repetitive Peak Forward Current	$t_p=1ms$	200	
$I^2t$		$T_J=125^{\circ}C, t=10ms, V_R=0V$	1650	$A^2S$

MacMic Science & Technology Co., Ltd.

Add: #18, Hua Shan Zhong Lu, New District, Changzhou City, Jiangsu Province, P. R .of China

# MMG100D170B6TC

## IGBT-inverter

### ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=4\text{mA}$	5.0	5.8	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		2.15	2.6	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.35		
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$		2.45		
$I_{CES}$	Collector Leakage Current	$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			1	mA
		$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$			10	mA
$I_{GES}$	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}, T_J=25^\circ\text{C}$	-500		500	nA
$R_{gint}$	Integrated Gate Resistor			3		$\Omega$
$Q_g$	Gate Charge	$V_{CE}=900\text{V}, I_C=100\text{A}, V_{GE}=15\text{V}$		0.72		$\mu\text{C}$
$C_{ies}$	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		9.5		nF
$C_{res}$	Reverse Transfer Capacitance				340	
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=900\text{V}, I_C=100\text{A}$ $R_G=5.1\Omega,$	$T_J=25^\circ\text{C}$		70	ns
			$T_J=150^\circ\text{C}$		90	ns
$t_r$	Rise Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		50	ns
			$T_J=150^\circ\text{C}$		55	ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=900\text{V}, I_C=100\text{A}$ $R_G=5.1\Omega,$	$T_J=25^\circ\text{C}$		460	ns
			$T_J=150^\circ\text{C}$		520	ns
$t_f$	Fall Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		200	ns
			$T_J=150^\circ\text{C}$		360	ns
$E_{on}$	Turn on Energy	$V_{CC}=900\text{V}, I_C=100\text{A}$ $R_G=5.1\Omega,$	$T_J=25^\circ\text{C}$		35	mJ
			$T_J=125^\circ\text{C}$		46	mJ
			$T_J=150^\circ\text{C}$		50	mJ
$E_{off}$	Turn off Energy	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$		16	mJ
			$T_J=125^\circ\text{C}$		25	mJ
			$T_J=150^\circ\text{C}$		27	mJ
$I_{SC}$	Short Circuit Current	$t_{psc} \leq 10\mu\text{s}, V_{GE}=15\text{V}$ $T_J=150^\circ\text{C}, V_{CC}=1000\text{V}$		480		A
$R_{thJC}$	Junction to Case Thermal Resistance (Per IGBT)				0.19	K/W

## Diode-inverter

### ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.8	2.2	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.9		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.9		
$t_{rr}$	Reverse Recovery Time	$I_F=100\text{A}, V_R=900\text{V}$ $dI_F/dt=-1850\text{A}/\mu\text{s}$ $T_J=150^\circ\text{C}$		750		ns
$I_{RRM}$	Max. Reverse Recovery Current			110		A
$Q_{RR}$	Reverse Recovery Charge			46		$\mu\text{C}$
$E_{rec}$	Reverse Recovery Energy			22		mJ
$R_{thJCD}$	Junction to Case Thermal Resistance (Per Diode)				0.32	K/W

# MMG100D170B6TC

MODULE CHARACTERISTICS ( $T_C=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit	
$T_{Jmax}$	Max. Junction Temperature	175	$^\circ\text{C}$	
$T_{Jop}$	Operating Temperature	-40~150		
$T_{stg}$	Storage Temperature	-40~125		
$V_{isol}$	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), $t=1$ minute	4000	V
CTI	Comparative Tracking Index		> 225	
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M6)	2.5~5	Nm
Weight			300	g

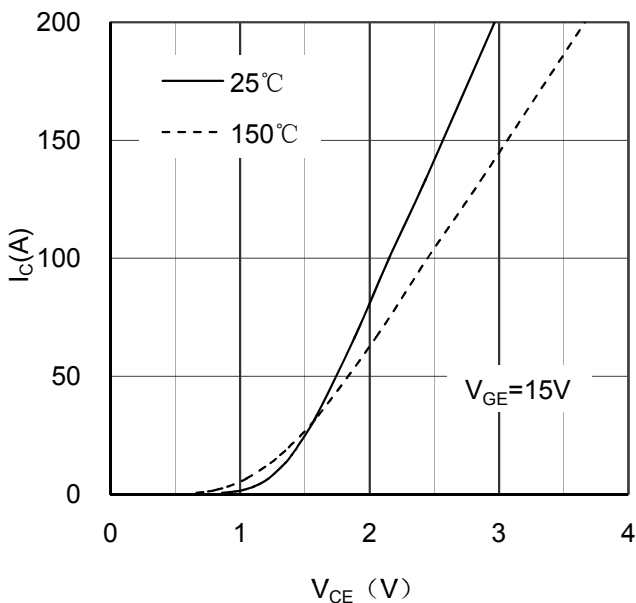


Figure 1. Typical Output Characteristics IGBT-inverter

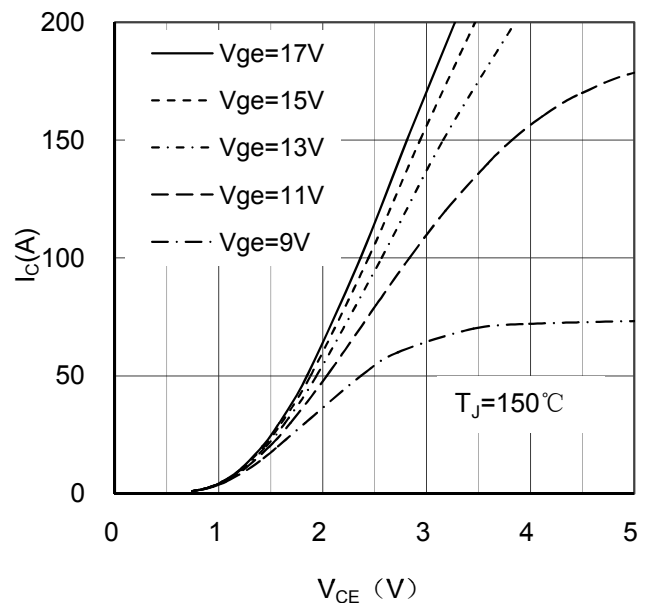


Figure 2. Typical Output Characteristics IGBT-inverter

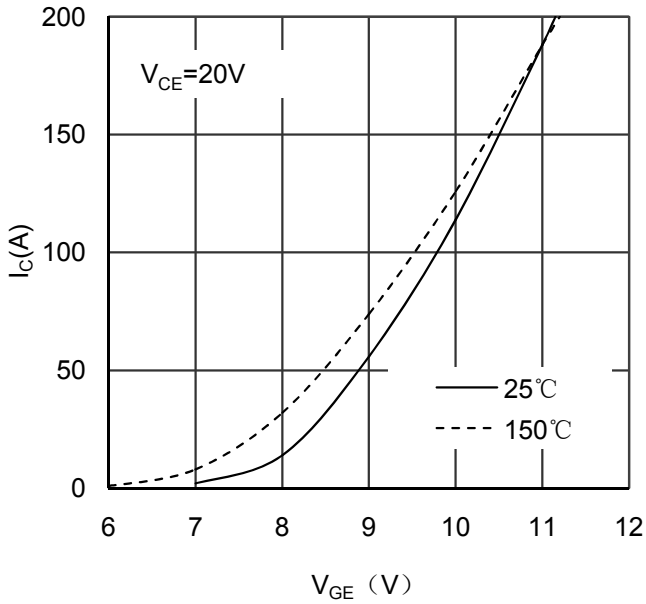


Figure 3. Typical Transfer characteristics IGBT-inverter

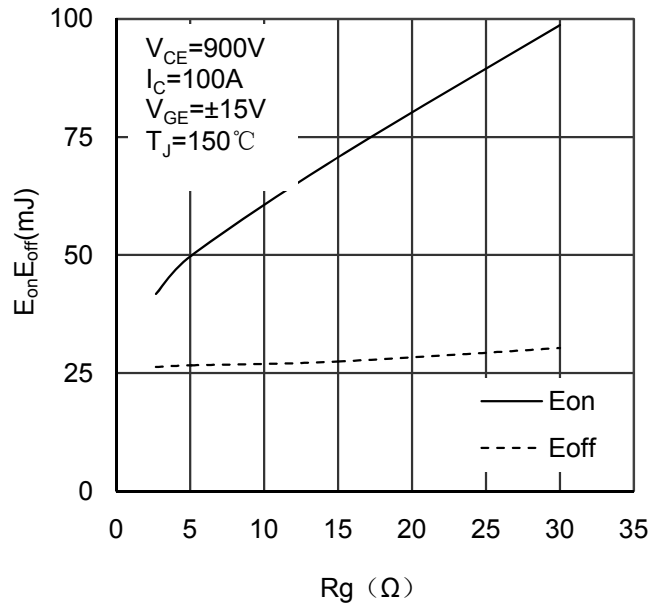


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

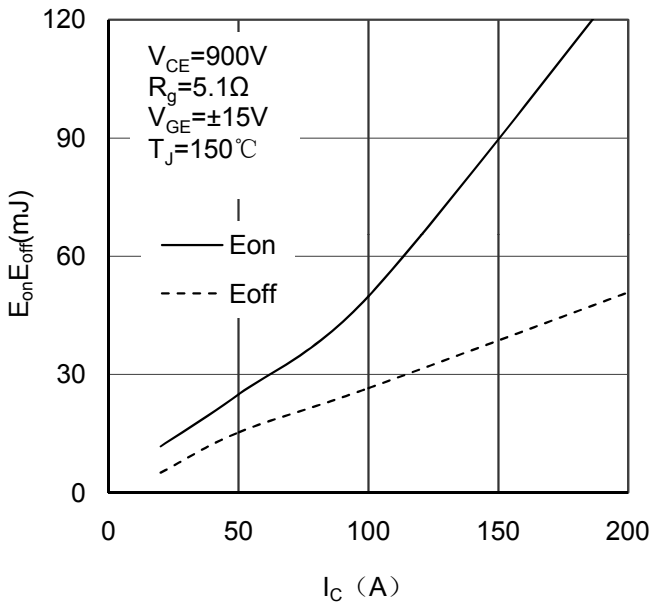


Figure 5. Switching Energy vs Collector Current IGBT-inverter

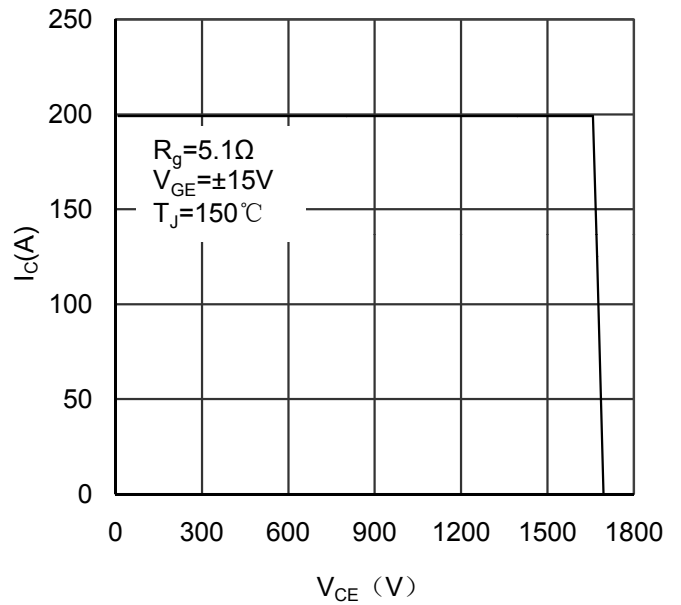


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

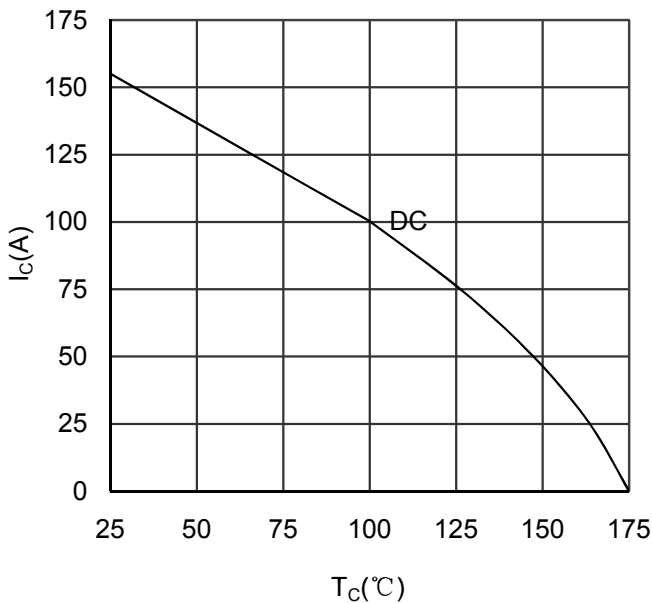


Figure 7. Collector Current vs Case temperature IGBT -inverter

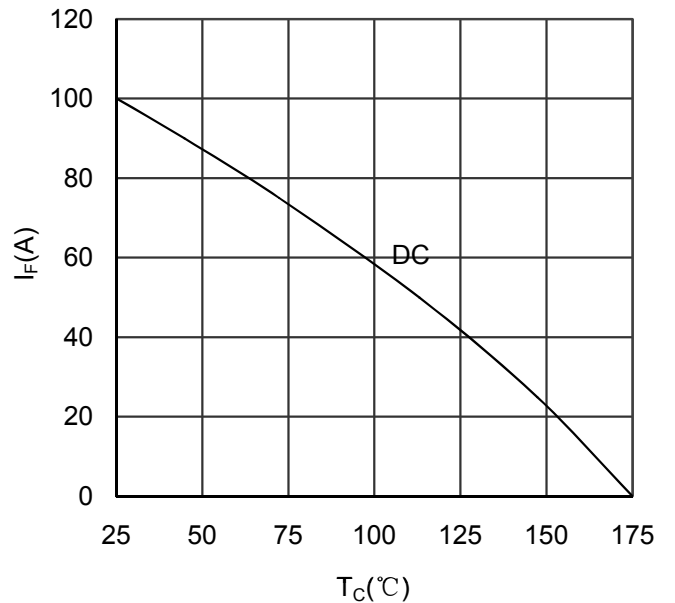


Figure 8. Forward current vs Case temperature Diode -inverter

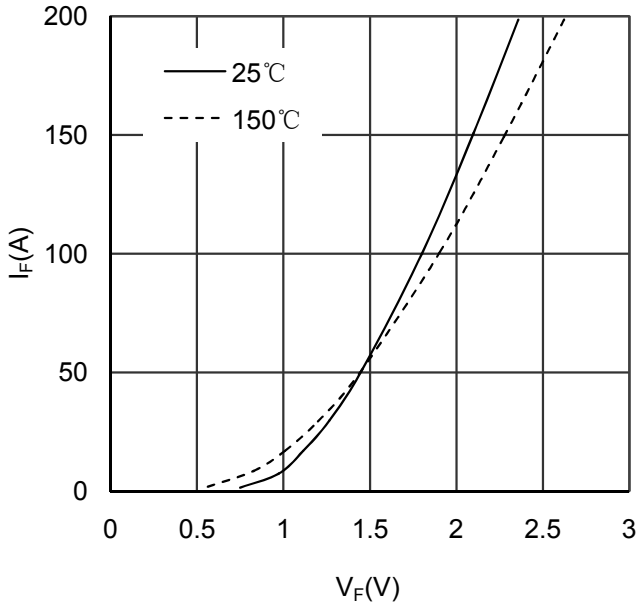


Figure 9. Diode Forward Characteristics Diode -inverter

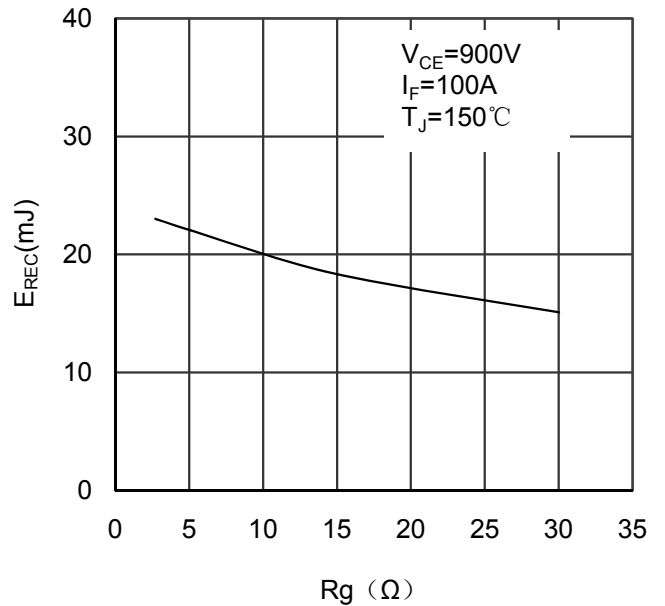


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

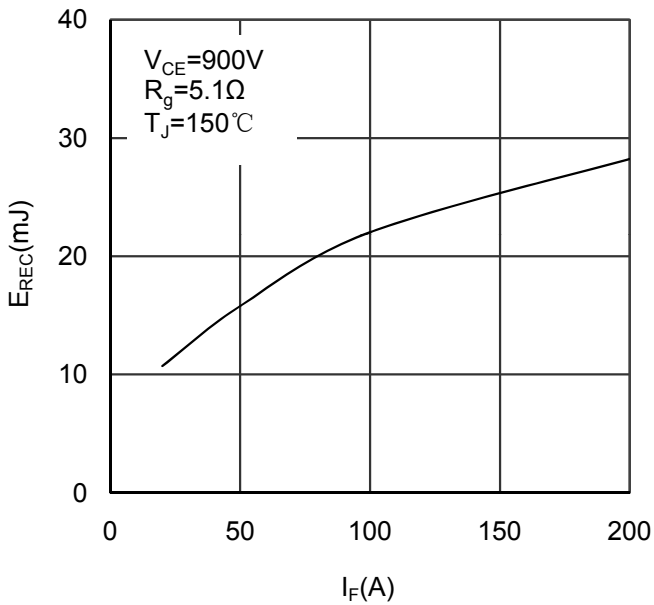


Figure 11. Switching Energy vs Forward Current Diode-inverter

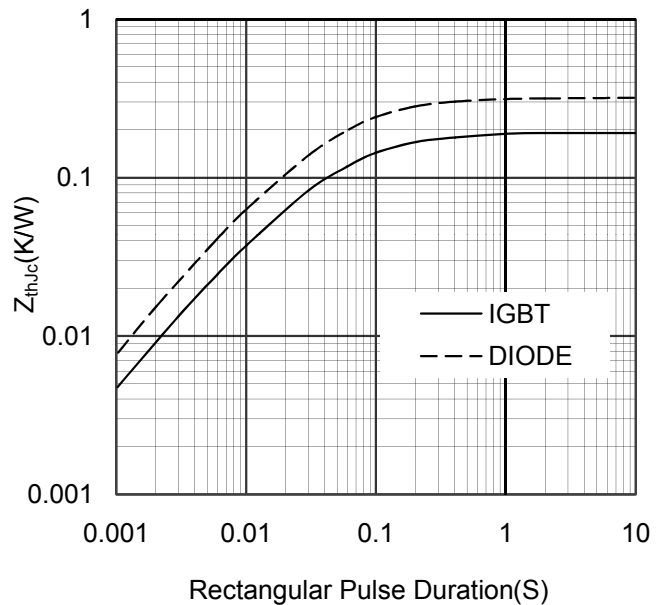


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

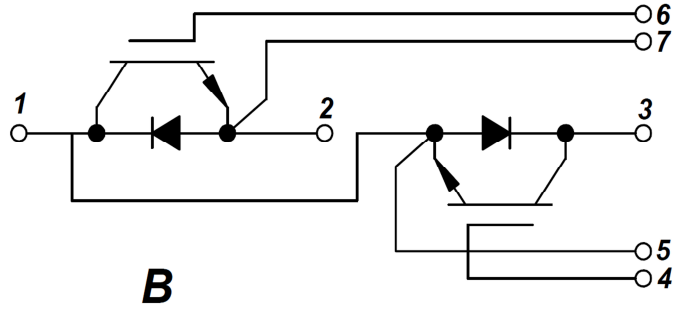
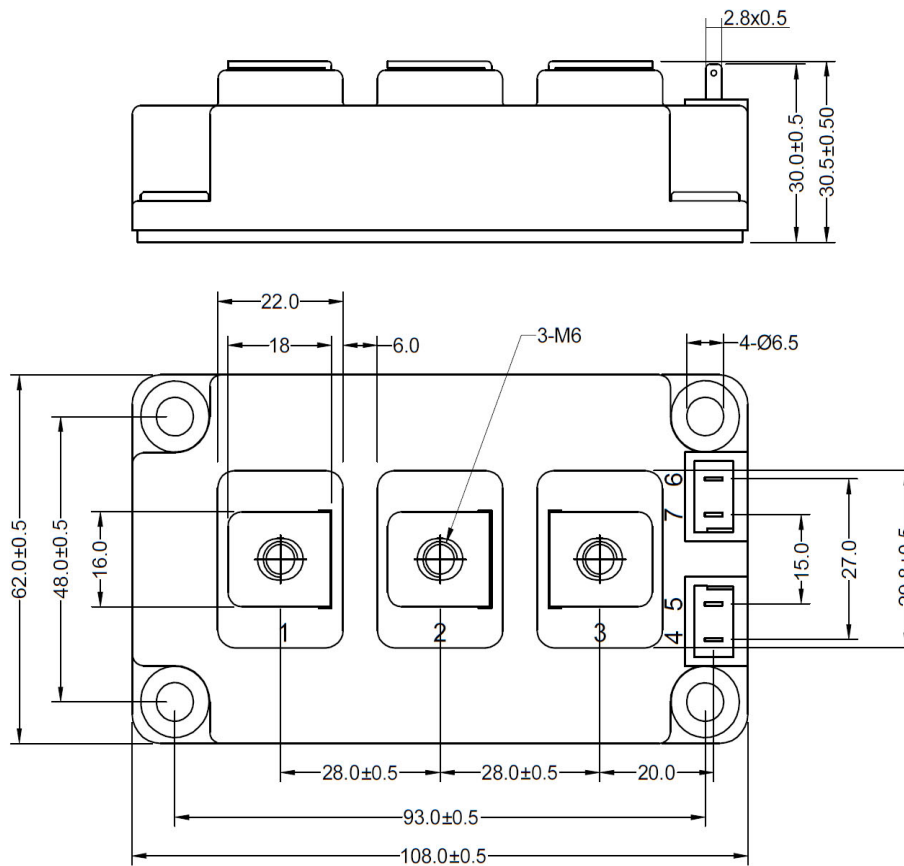


Figure 13. Circuit Diagram



Dimensions in (mm)

Figure 14. Package Outline